HY5116164B Series

1M x 16-bit CMOS DRAM with Extended Data Out

DESCRIPTION

The HY5116164B is the new generation and fast dynamic RAM organized 1,048,576 x 16-bit. The HY5116164B utilizes Hyundai's CMOS silicon gate process technology as well as advanced circuit techniques to provide wide operating margins to the users. Multiplexed address inputs permit the HY5116164B to be packaged in standard 42/42 pin plastic SOJ, 44/50 pin TSOP-II and Reverse TSOP-II.
The package size provides high system bit densities and is compatible with widely available automated testing and insertion equipments. System oriented feature includes single power supply of 5V± 10% tolerence and direct interfacing capability with high performance logic families such as Schottky TTL.

FEATURES

- **Low power dissipation**
  Max. CMOS standby 2.8mW (SL-part)
  5.5mW
  Max. TTL standby 11.0mW
  Max. operating

Speed	Power
60	550mW
70	495mW
80	440mW

- **Single power supply of 5V±10%**
- **TTL compatible inputs and outputs**
- **Fast access and cycle time**

Speed	tRAC	tCAC	tHPC
60	60ns	15ns	25ns
70	70ns	20ns	30ns
80	80ns	20ns	35ns

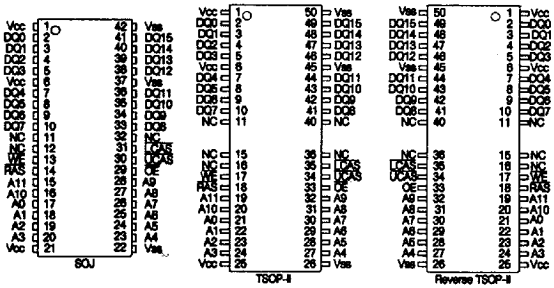
- **Extended Data Out operation**
- **2$\overline{CAS}$ Inputs for upper and lower byte conrtol**
- **Read-Modify-Write capability**
- **$\overline{CAS}$-before-$\overline{RAS}$, $\overline{RAS}$-only, Hidden refresh and Self refresh capability**
- **4096 refresh cycles /256ms (SL-part)**
  4096 refresh cycles /64ms

PIN DESCRIPTION

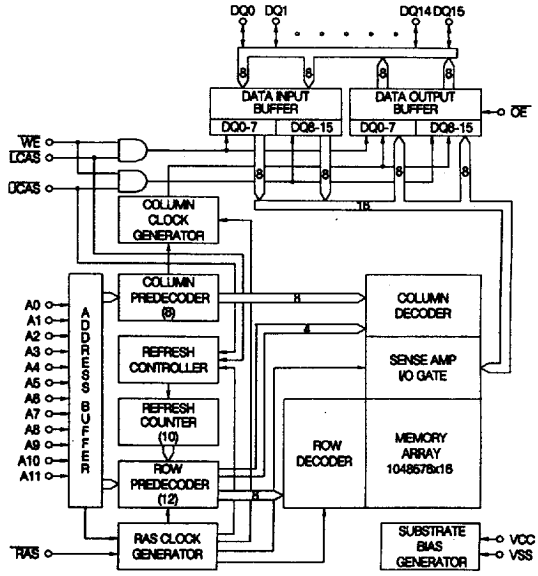
$\overline{RAS}$	Row Address Strobe
$\overline{LCAS}$, $\overline{UCAS}$	Column Address Strobe
$\overline{WE}$	Write Enable
$\overline{OE}$	Output Enable
A0 - A11*	Address Input
DQ0 - DQ15	Data Input/Output
Vcc	Power (+5V)
Vss	Ground

* A8-A11 are applied to low address input only.

PIN CONNECTION



BLOCK DIAGRAM



ABSOLUTE MAXIMUM RATING

SYMBOL	PARAMETER	RATING	UNIT
T_A	Ambient Temperature	0 to 70	°C
T_{STG}	Storage Temperature	-55 to 150	°C
V_{IN}, V_{OUT}	Voltage on Any Pin Relative to Vss	-1.0 to 7.0	V
V_{CC}	Voltage on Vcc Relative to Vss	-1.0 to 7.0	V
I_{OS}	Short Circuit Output Current	50	mA
P_D	Power Dissipation	0.70	W
T_{SOLDER}	Soldering Temperature • Time	260 • 10	°C • sec

NOTE:Operation at or above Absolute Maximum Ratings can adversely affect device reliability.

RECOMMENDED DC OPERATING CONDITIONS

(T_A = 0°C to 70°C)

SYMBOL	PARAMETER	MIN.	TYP.	MAX.	UNIT
V_{CC}	Power Supply Voltage	4.5	5.0	5.5	V
V_{SS}	Ground	0	0	0	V
V_{IH}	Input High Voltage	2.4	-	Vcc+1.0	V
V_{IL}	Input Low Voltage	-1.0	-	0.8	V

NOTE: All Voltage are referenced to Vss.

DC CHARACTERISTICS

(T_A=0°C to 70°C, V_{CC}=5V±10%, V_{SS}=0V, unless otherwise noted.)

SYMBOL	PARAMETER	TEST CONDITIONS	SPEED/ POWER	MIN.	MAX.	UNIT	NOTE
I_{LI}	Input Leakage Current (Any Input Pins)	$V_{SS} \le V_{IN} \le V_{CC}$+1.0V, All other pins not under test = Vss		-10	10	µA	
I_{LO}	Output Leakage Current (High impedance State)	$V_{SS} \le V_{OUT} \le V_{CC}$ $\overline{RAS}$ & $\overline{CAS}$ at V_{IH}		-10	10	µA	
I_{CC1}	Vcc Supply Current, Operating	t_{RC} = t_{RC} (min.)	60 70 80	- - -	100 90 80	mA	1,2,3
I_{CC2}	Vcc Supply Current, TTL Standby	$\overline{RAS}$ & $\overline{CAS}$ at V_{IH}, other inputs ≥ Vss	 SL-part	- -	2 1	mA	
I_{CC3}	Vcc Supply Current, $\overline{RAS}$-only refresh	t_{RC} = t_{RC} (min.)	60 70 80	- - -	100 90 80	mA	1,3
I_{CC4}	Vcc Supply Current, EDO mode	t_{HPC} = t_{HPC} (min.)	60 70 80	- - -	140 120 100	mA	1,2,3
I_{CC5}	Vcc Supply Current, CMOS Standby	$\overline{RAS}$ & $\overline{CAS}$ ≥Vcc-0.2V	 SL-part	- -	1 300	mA µA	5
I_{CC6}	Vcc Supply Current, $\overline{CAS}$-before- $\overline{RAS}$ refresh	t_{RC} = t_{RC} (min.)	60 70 80	- - -	100 90 80	mA	1,2
I_{CC7}	Vcc Supply Current, Battery Back up (SL-part only)	t_{RC} = 62.5µs, $\overline{RAS}$ = CBR cycling or 0.2V, $\overline{OE}$ & $\overline{WE}$ = Vcc-0.2V or 0.2V A0-A11 = Vcc-0.2V or 0.2V, DQ0-DQ15 = 0.2V, Vcc-0.2V or open	t_{RAS} ≤ 300ns t_{RAS} ≤ 1µs	- -	350 450	µA	4,5
I_{CC8}	Vcc Supply Current, Self Refresh (SL-Part only)	$\overline{RAS}$ & $\overline{CAS}$ ≤ 0.2V other pins same as I_{CC7}		-	350	µA	5
V_{OL}	Output Low Voltage	I_{OL} = 4.2mA		-	0.4	V	
V_{OH}	Output High Voltage	I_{OH} = -5.0mA		2.4	-	V	

NOTE :

1. I_{CC1}, I_{CC3}, I_{CC4} and I_{CC6} depend on cycle rate.
2. I_{CC1}, I_{CC3}, I_{CC4} and I_{CC6} are depend on output loading. Specified values are obtained with the output open.
3. I_{CC} is specified as average current. I_{CC1}, I_{CC3}, I_{CC6}, Address can be changed maximum two times while $\overline{RAS}$=V_{IL}. I_{CC4}, Address can be changed maximum once while $\overline{CAS}$=V_{IH}.
4. Only t_{RAS}(max.)=1µs is applied to refresh of battery backup but t_{RAS}(max.)=10µs is applied to normal functional operation.
5. I_{CC5}(max.)=300µA, I_{CC7} and I_{CC8} are applied to SL-parts only.

AC CHARACTERISTICS

(TA=0°C to 70°C, Vcc=5V ± 10%, Vss=0V, unless otherwise noted.)

#	SYMBOL	PARAMETER	HY5116164BJC/TC/RC/SLJC/SLTC/SLRC						UNIT	NOTE
			-60		-70		-80			
			MIN	MAX	MIN	MAX	MIN	MAX		
1	tRC	Random Read or Write Cycle Time	105	-	125	-	145	-	ns	
2	tRWC	Read-Modify-Write Cycle Time	142	-	167	-	187	-	ns	
3	tHPC	EDO Mode Cycle Time	25	-	30	-	35	-	ns	
4	tHPRWC	EDO Mode Read-Modify-Write Cycle Time	73	-	85	-	100	-	ns	
5	tRAC	Access Time form $\overline{RAS}$	-	60	-	70	-	80	ns	8,9,10
6	tCAC	Access Time from $\overline{CAS}$	-	15	-	20	-	20	ns	8,9
7	tAA	Access Time from Column Address	-	30	-	35	-	40	ns	8,10
8	tCPA	Access Time from $\overline{CAS}$ Precharge		35		35		40	ns	8,15
9	tCLZ	$\overline{CAS}$ to Output Low Impedance	0	-	0	-	0	-	ns	8
10	tOFF	Output Buffer Turn-off Delay	0	15	0	15	0	15	ns	11
11	tT	Transition Time (Rise and Fall)	2.5	50	2.5	50	2.5	50	ns	6
12	tRP	$\overline{RAS}$ Precharge Time	40	-	50	-	60	-	ns	
13	tRAS	$\overline{RAS}$ Pulse Width	60	10K	70	10K	80	10K	ns	
14	tRASP	$\overline{RAS}$ Pulse Width (EDO Mode)	60	100K	70	100K	80	100K	ns	
15	tRSH	$\overline{RAS}$ Hold Time	13	-	15	-	20	-	ns	
16	tCSH	$\overline{CAS}$ Hold Time	40	-	50	-	60	-	ns	
17	tCAS	$\overline{CAS}$ Pulse width	13	10K	15	10K	20	10K	ns	
18	tRCD	$\overline{RAS}$ to $\overline{CAS}$ Delay	20	45	20	50	20	60	ns	9
19	tRAD	$\overline{RAS}$ to Column Address Delay Time	15	30	15	35	15	40	ns	10
20	tCRP	$\overline{CAS}$ to $\overline{RAS}$ Precharge Time	5	-	5	-	5	-	ns	15
21	tCP	$\overline{CAS}$ Precharge Time	7	-	10	-	10	-	ns	20
22	tASR	Row Address Set-up Time	0	-	0	-	0	-	ns	
23	tRAH	Row Address Hold time	10	-	10	-	10	-	ns	
24	tASC	Column Address Set-up Time	0	-	0	-	0	-	ns	15
25	tCAH	Column Address Hold Time	10	-	15	-	15	-	ns	15
26	tRAL	Column Address to $\overline{RAS}$ Lead Time	30	-	35	-	40	-	ns	
27	tRCS	Read Command Set-up Time	0	-	0	-	0	-	ns	15
28	tRCH	Read Command Hold Time Referenced to $\overline{CAS}$	0	-	0	-	0	-	ns	13,15
29	tRRH	Read Command Hold Time Referenced to $\overline{RAS}$	0	-	0	-	0	-	ns	15
30	tWCH	Write Command Hold Time	10	-	15	-	15	-	ns	15
31	tWP	Write Command Pulse Width	10	-	10	-	10	-	ns	
32	tRWL	Write Command to $\overline{RAS}$ Lead Time	15	-	15	-	15	-	ns	
33	tCWL	Write Command to $\overline{CAS}$ Lead Time	13	-	15	-	20	-	ns	22
34	tDS	Data-In Set-up Time	0	-	0	-	0	-	ns	15,25
35	tDH	Data-In Hold Time	10	-	15	-	15	-	ns	15,25
36	tREF	Refresh Period (4096cycle)	-	64	-	64	-	64	ms	18
		SL-Part	-	256	-	256	-	256	ms	
37	tWCS	Write Command Set-up Time	0	-	0	-	0	-	ns	15,16
38	tCWD	$\overline{CAS}$ to $\overline{WE}$ Delay Time	37	-	45	-	45	-	ns	16,21
39	tRWD	$\overline{RAS}$ to $\overline{WE}$ Delay Time	80	-	95	-	105	-	ns	16
40	tAWD	Column Address to $\overline{WE}$ Delay Time	50	-	60	-	65	-	ns	16

AC CHARACTERISTICS

(continued)

#	SYMBOL	PARAMETER	HY5116164BJC/TC/RC/SLJC/SLTC/SLRC						UNIT	NOTE
			-60		-70		-80			
			MIN	MAX	MIN	MAX	MIN	MAX		
41	tCSR	$\overline{CAS}$ Set-up Time (CBR Cycle)	5	-	5	-	5	-	ns	15
42	tCHR	$\overline{CAS}$ Hold Time (CBR Cycle)	10	-	10	-	10	-	ns	15
43	tRPC	$\overline{RAS}$ to $\overline{CAS}$ Precharge Time	5	-	5	-	5	-	ns	15
44	tCPT	$\overline{CAS}$ Precharge Time (CBR Counter Test)	30	-	35	-	40	-	ns	20
45	tROH	$\overline{RAS}$ Hold Time Referenced to $\overline{OE}$	10	-	10	-	10	-	ns	
46	tOEA	$\overline{OE}$ Access Time	-	17	-	20	-	20	ns	
47	tOED	$\overline{OE}$ to Data Delay	15	-	20	-	20	-	ns	
48	tOEZ	Output Buffer Turn Off Delay Time	0	15	0	15	0	15	ns	11
49	tOEH	$\overline{OE}$ Command Hold Time	15	-	20	-	20	-	ns	
50	tCPWD	$\overline{WE}$ Delay Time from $\overline{CAS}$ Precharge	55	-	65	-	75	-	ns	16
51	tRHCP	$\overline{RAS}$ Hold Time from $\overline{CAS}$ Precharge	35	-	40	-	50	-	ns	
52	tWRP	$\overline{WE}$ to $\overline{RAS}$ Precharge Time (CBR Cycle)	10	-	10	-	10	-	ns	
53	tWRH	$\overline{WE}$ to $\overline{RAS}$ Hold Time (CBR Cycle)	10	-	10	-	10	-	ns	
54	tRASS	$\overline{RAS}$ Pulse Width (Self Refresh Cycle)	100	-	100	-	100	-	µs	
55	tRPS	$\overline{RAS}$ Precharge Time (Self Refresh Cycle)	110	-	130	-	150	-	ns	
56	tCHS	$\overline{CAS}$ Hold Time (Self Refresh Cycle)	50	-	50	-	50	-	ns	
57	tDOH	Output Data Hold Time	5	-	5	-	5	-	ns	
58	tREZ	Output Buffer Turn Off Delay Time from $\overline{RAS}$	0	15	0	15	0	15	ns	
59	tWEZ	Output Buffer Turn Off Delay Time from $\overline{WE}$	0	15	0	15	0	15	ns	
60	tWED	$\overline{WE}$ to Data Delay Time	15	-	15	-	15	-	ns	
61	tOEP	$\overline{OE}$ Hold Pulse Width	10	-	10	-	10	-	ns	
62	tWPE	$\overline{WE}$ Pulse Width (EDO Cycle)	10	-	10	-	10	-	ns	
63	tOCH	$\overline{OE}$ to $\overline{CAS}$ Hold Time	0	-	0	-	0	-	ns	
64	tCHO	$\overline{CAS}$ Hold Time to $\overline{OE}$	5	-	5	-	5	-	ns	

NOTE:

1. Stress greater than those listed under "Absolute Maximum Ratings" may cause permanent damage to the device.
2. All voltages referenced to V_{SS}.
3. An initial pause of 200μs is required after power-up followed by 8 $\overline{RAS}$ only refresh cycles before proper device operation is achieved. In case of using internal refresh counter, a minimum of 8 $\overline{CAS}$ before $\overline{RAS}$ refresh cycles instead of 8 $\overline{RAS}$ only refresh cycles are required.
4. Address can be changed once or less while $\overline{RAS}$ = V_{IL}. In case of changed once or less during a EDO mode cycle (t_{HPC}).
5. AC measurements assume t_T 2.5ns.
6. V_{IH}(min.) and V_{IL}(max.) are reference levels for measuring timing of input signals. Also, transition times are measured between V_{IH} and V_{IL}.
7. The minimum specifications are used only to indicate cycle time at which proper operation over the full temperature range (T_A = 0 to 70°C) is assured.
8. Measured at V_{OH}=2.0V and V_{OL}=0.8V with a load equivalent to 2TTL load and 100pF.
9. Operation within the t_{RCD}(max.) limit insures that t_{RAC}(max.) can be met.
   t_{RCD}(max.) is specified as a reference point only. If t_{RCD} is greater than the specified t_{RCD}(max.) limit, then access time is controlled by t_{CAC}.
10. Operation within the t_{RAD}(max.) limit insures that t_{RAC}(max.) can be met.
    t_{RAD}(max.) is specified as a reference point only. If t_{RAD} is greater than the specified t_{RAD}(max.) limit, hen access time is controlled by t_{AA}.
11. t_{OFF}(max.), t_{REZ}(max.), t_{WEZ}(max.) and t_{OEZ}(max.) define the time at which the output achieves the open circuit condition and are not referenced to output voltage levels.
12. The t_{CRP} requirement should be applicable for $\overline{RAS}$ / $\overline{CAS}$ cycles preceded by any cycle.
13. Either t_{RCH} or t_{RRH} must be satisfied for a read cycle.
14. Parameter t_{WP} is a applicable for a late write cycle. For early write cycle., t_{WCH} must be met.
15. These parameters are referenced to $\overline{UCAS}$ or $\overline{LCAS}$ leading edge in early write cycles and to $\overline{WE}$ leading edge in Read-Modify-Write cycles.
16. t_{WCS}, t_{RWD}, t_{CWD}, t_{AWD}, and t_{CPWD} are not restrictive operating parameters. They are included in the data sheet as electrical characteristics only. If $t_{WCS} \geq t_{WCS}$(min.), the cycle is an early write cycle and the data output pin will remain open circuit(high impedance) through the entire cycle. If $t_{RWD} \geq t_{RWD}$(min.), $t_{CWD} \geq t_{CWD}$(min.), $t_{AWD} \geq t_{AWD}$(min.), and $t_{CPWD} \geq t_{CPWD}$(min.) (Hyper Page Mode), the cycle is a Read-Modify-Write cycle and the data out will contain data read from the selected cell. If neither of the above sets of condition of the data out (at access time) is interminated.
17. If $\overline{RAS}$ goes to high before $\overline{CAS}$ high going, the open circuit condition of the output is achieved by $\overline{CAS}$ high going. If $\overline{CAS}$ goes to high before RAS high going, the open circuit condition of the output is achieved by $\overline{RAS}$ high going.
18. 4096 cycles of Burst Refresh must be excuted within 64ms after exiting Self Refresh.
19. t_{ASC}, t_{CAH} are reference to the earlier $\overline{CAS}$ falling edge.
20. t_{CP} and t_{CPT} are measured when both $\overline{LCAS}$ and $\overline{UCAS}$ are high state.
21. t_{CWD} is referenced to the later $\overline{CAS}$ falling edge at word read-modify-write cycle.
22. t_{CWL} must be satisfied by both $\overline{LCAS}$ and $\overline{UCAS}$ for 16-bits access cycles.
23. t_{CSR} is referenced to earlier $\overline{CAS}$ falling low before $\overline{RAS}$ transition low.
24. t_{CHR} is referenced to the later $\overline{CAS}$ rising high after $\overline{RAS}$ transition low.
25. t_{DS}, t_{DH} is independetly specified for lower byte DQ(0-7), upper byteDQ(8-15).

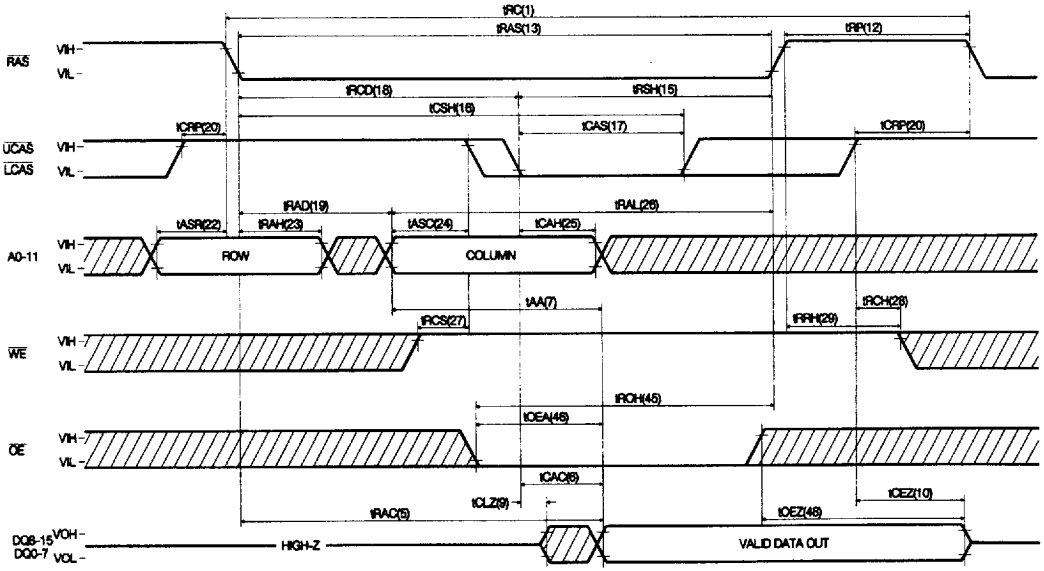
CAPACITANCE

(T_A=25°C, Vcc=5.0V±10%, Vss=0V, f=1MHz, unless otherwise noted.)

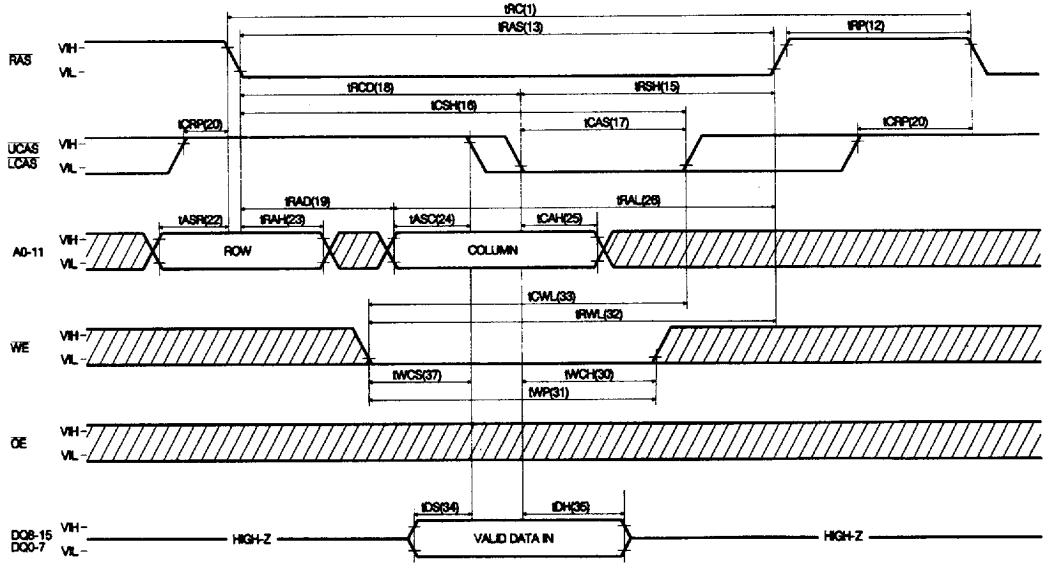
SYMBOL	PARAMETER	TYP.	MAX.	UNIT
C_{IN1}	Input Capacitance (A0-A11)	-	5	pF
C_{IN2}	Input Capacitance ($\overline{RAS}$,$\overline{LCAS}$,$\overline{UCAS}$,$\overline{WE}$,$\overline{OE}$)	-	7	pF
C_{DQ}	Data Input/Output Capacitance (DQ0-DQ15)	-	7	pF

TIMING DIAGRAM

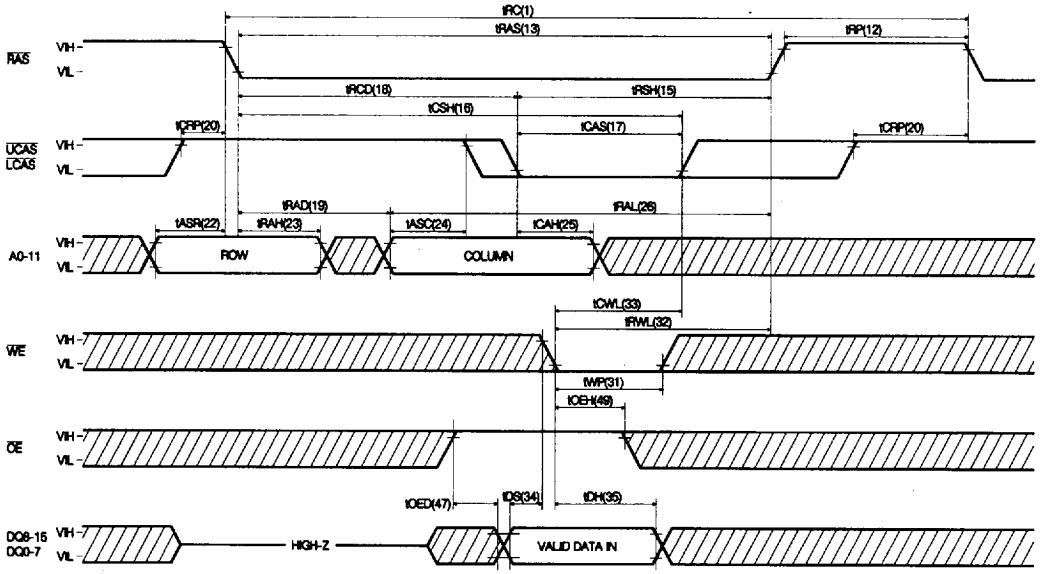
READ CYCLE



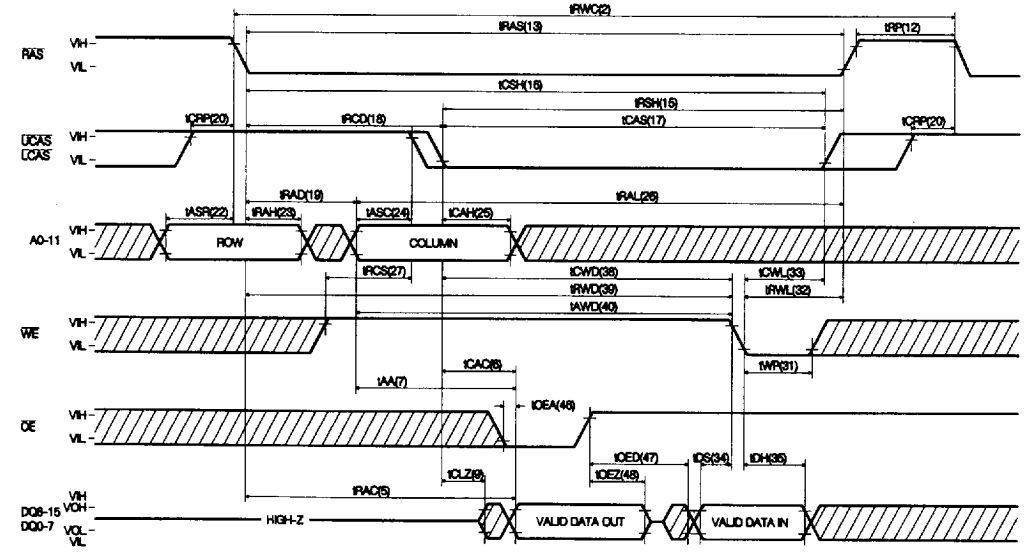
EARLY WRITE CYCLE



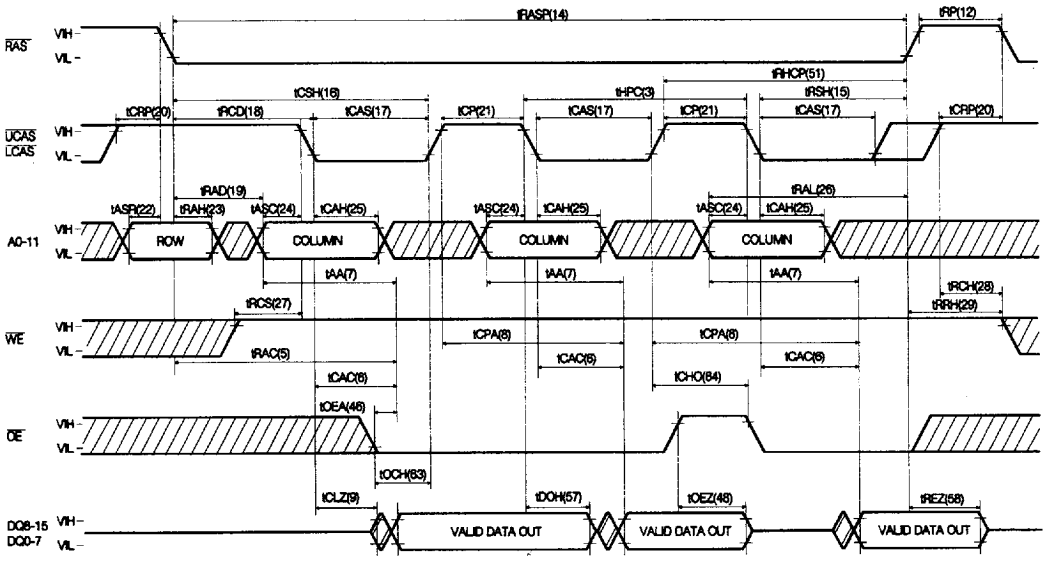
WRITE CYCLE ($\overline{OE}$ CONTROLLED WRITE)



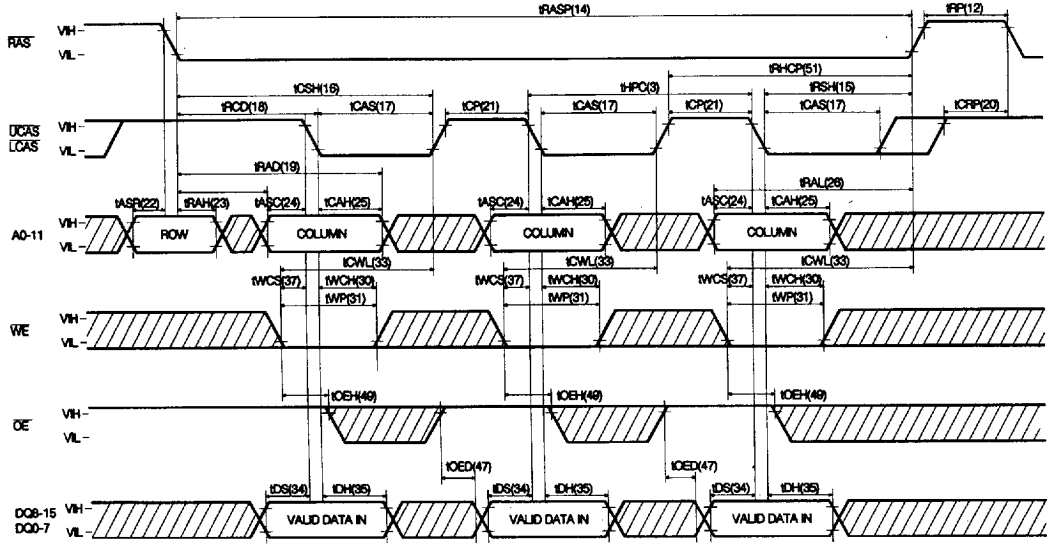
READ-MODIFY-WRITE CYCLE



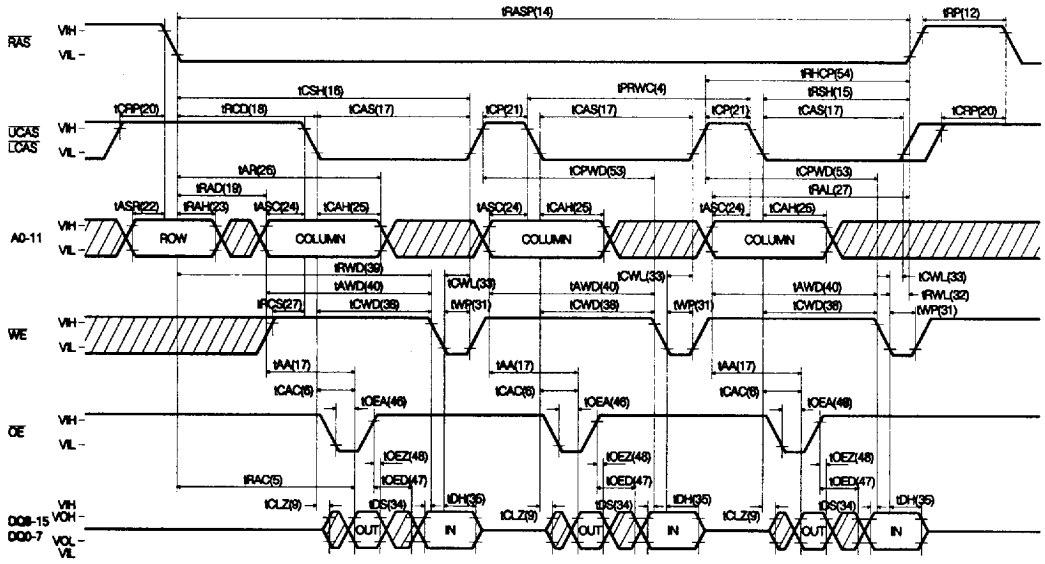
EDO MODE READ CYCLE



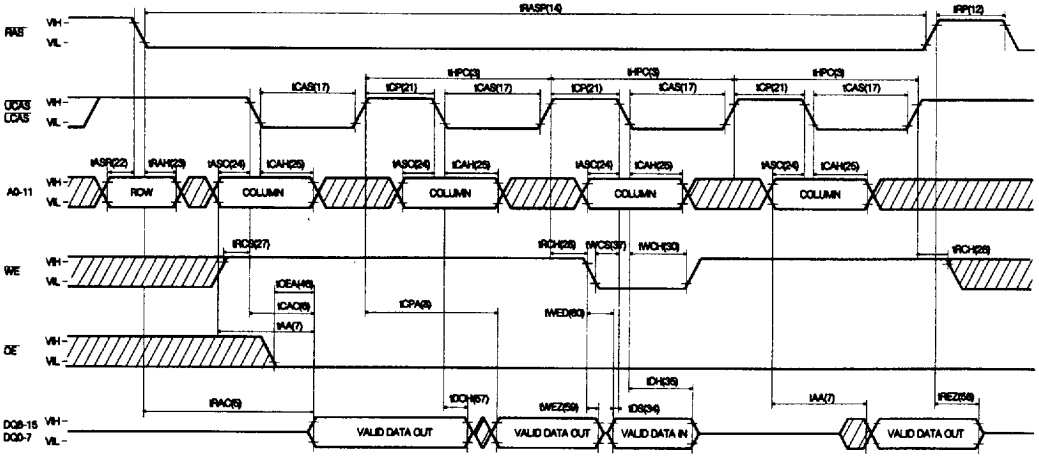
EDO MODE EARLY WRITE CYCLE



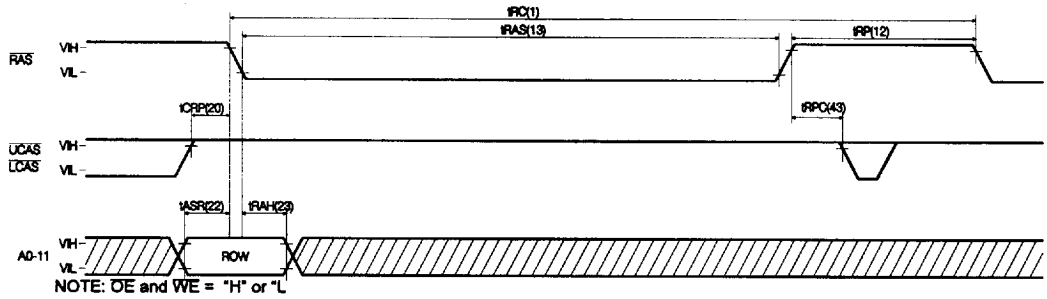
EDO MODE READ-MODIFY-WRITE CYCLE



EDO MODE AND WRITE MIXED CYCLE

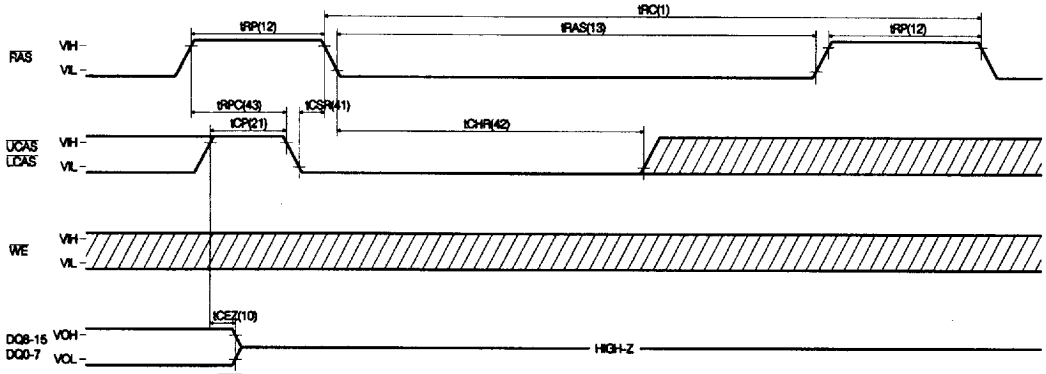


$\overline{RAS}$-ONLY REFRESH CYCLE



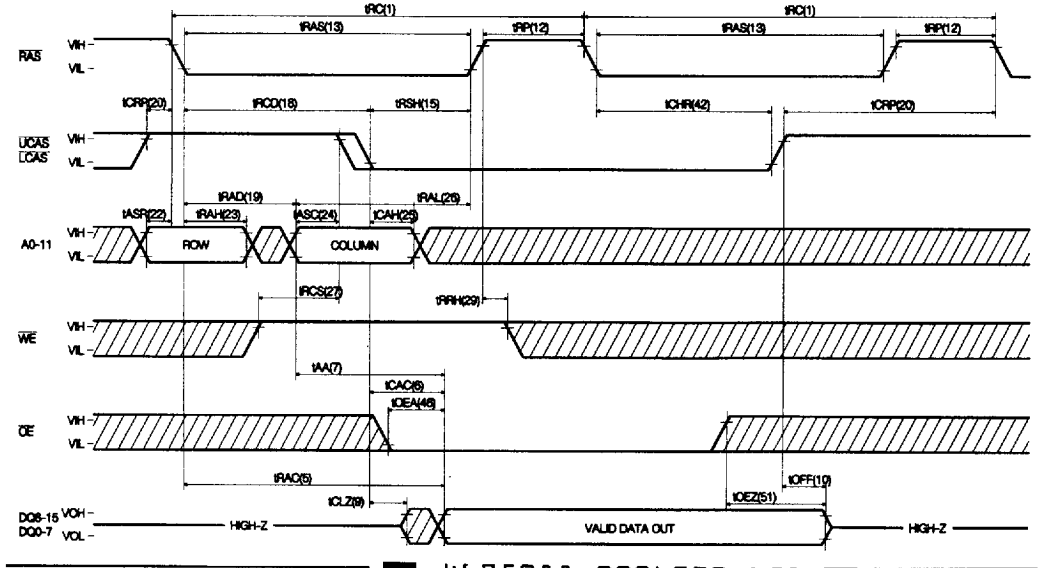
NOTE: $\overline{OE}$ and $\overline{WE}$ = "H" or "L"

$\overline{CAS}$-BEFORE-$\overline{RAS}$ REFRESH CYCLE

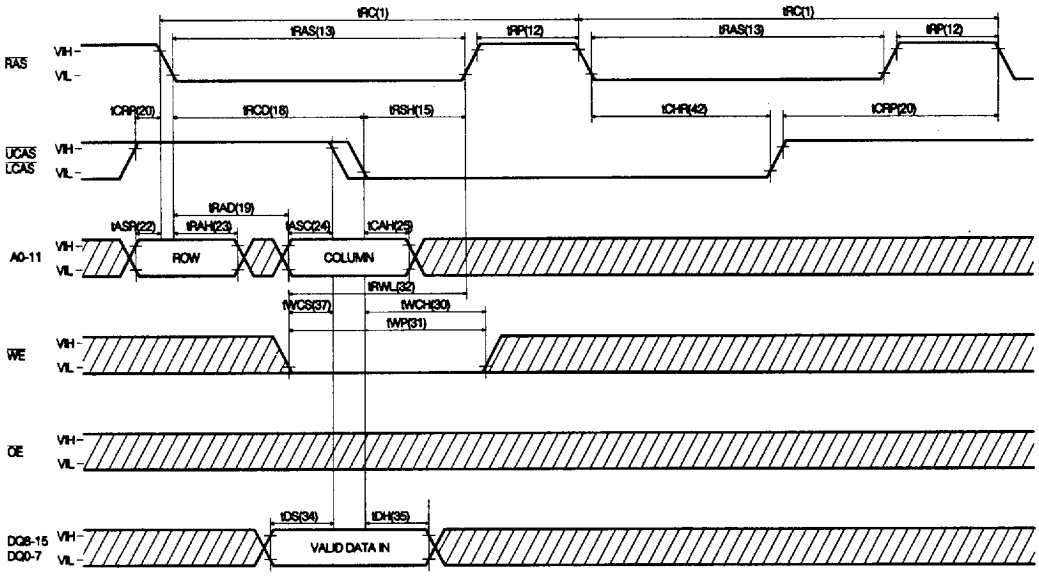


NOTE:A0-11 and $\overline{OE}$ = "H" or "L

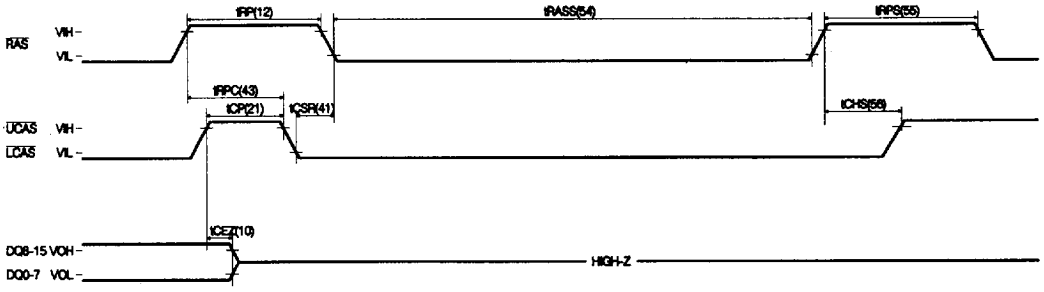
HIDDEN REFRESH CYCLE (READ)



HIDDEN REFRESH CYCLE (WRITE)

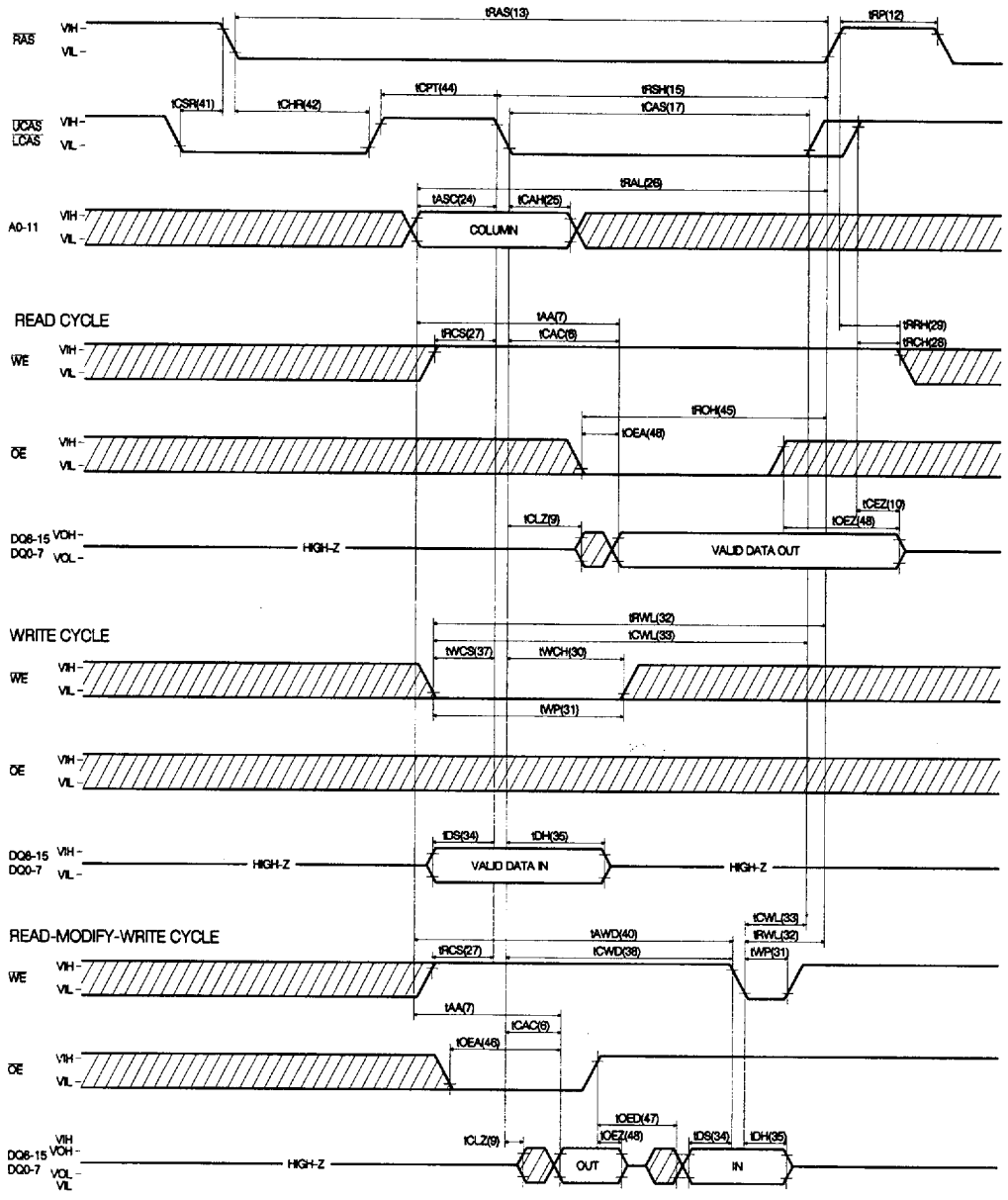


CAS-BEFORE-RAS SELF REFRESH CYCLE



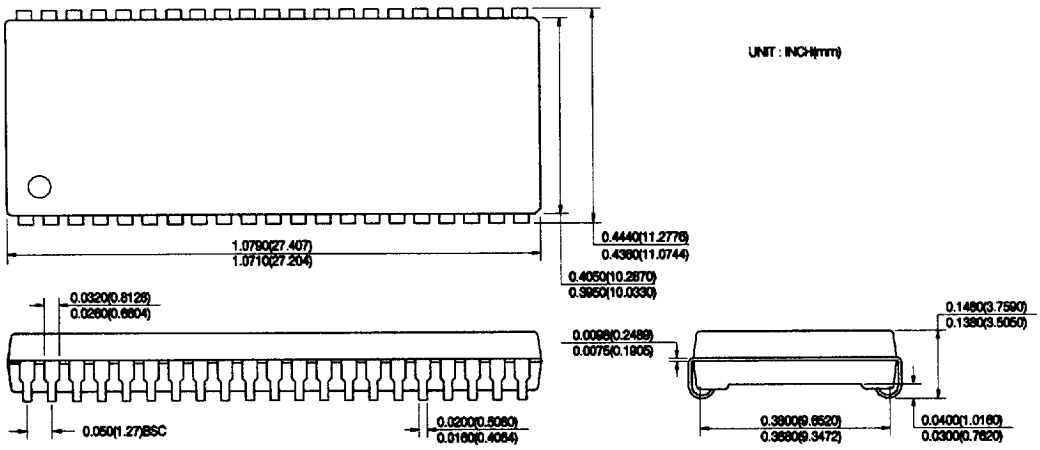
NOTE:A0-11, $\overline{OE}$ and $\overline{WE}$ = "H" or "L"

CAS-BEFORE-RAS REFRESH COUNTER TEST CYCLE

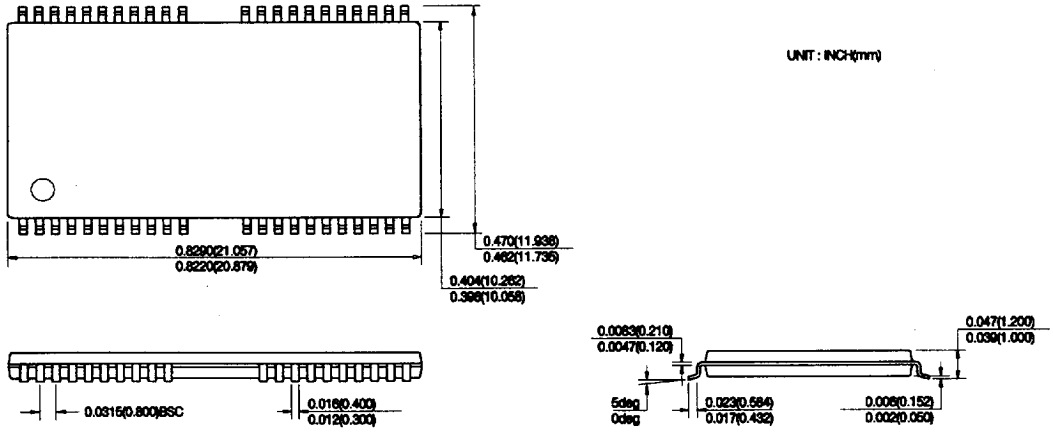


PACKAGE INFORMATION

400 mil 42/42 pin Small Outline J-form Package (JC)



400 mil 44/50 pin Thin Small Outline Package (TC) (RC)



ORDERING INFORMATION

PART NO	SOEED	POWER	PACKAGE
HY5116164BJC	60/70/80		SOJ
HY5116164BSLJC	60/70/80	SL-part	SOJ
HY5116164BTC	60/70/80		TSOP-II
HY5116164BSLTC	60/70/80	SL-part	TSOP-II
HY5116164BRC	60/70/80		TSOP-II(R)
HY5116164BSLRC	60/70/80	SL-part	TSOP-II(R)